

Optical transitions selection rules

- CB and VB symmetry and optical selection rules
- Optical transitions with linearly polarized light
- Optical transitions with circularly polarized light
- Optical spin orientation

1

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$$W_{if} = \frac{2\pi}{\hbar} \left(\frac{e E_0}{m_0 \omega} \right)^2 \left| \langle f | \vec{e} \cdot \vec{p} | i \rangle \right|^2 \delta(E_i - E_f)$$

$E_0 \Rightarrow$ AMPLITUDE ELECTRIC FIELD

FINAL STATE

INITIAL STATE

$$\langle f | \vec{e} \cdot \vec{p} | i \rangle$$

\vec{e}
POL VECTOR

$$\vec{p} = -i\hbar \vec{\nabla}$$

$$f = e^{i\vec{k}_f \cdot \vec{r}} u_f(\vec{r}) \quad i = e^{i\vec{k}_i \cdot \vec{r}} u_i(\vec{r})$$

$$\begin{aligned}
 \vec{e}^0 \cdot \langle A | \vec{p}^0 | i \rangle &= \vec{e}^0 \cdot \int e^{-i \hbar_A \vec{r}} \mu_A^*(r) \underline{-i \hbar \vec{\nabla}} \left(\underline{e^{i \hbar_i r}} \right) \\
 &= \vec{e}^0 \cdot \int e^{-i \hbar_A r} \mu_A^*(r) \hbar \vec{k}_i e^{i \hbar_i r} \mu_i(r) d^3 r + \\
 &\quad \parallel \emptyset \\
 \vec{e}^0 \cdot \int e^{-i \hbar_A r} e^{i \hbar_i r} \mu_A^*(r) -i \hbar \vec{\nabla} (\mu_i(r)) d^3 r
 \end{aligned}$$

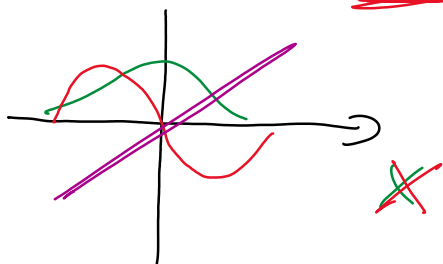
For direct Transitions $\hbar_A = \hbar_i$

$$\vec{e}^0 \cdot \int \mu_A^*(r) -i \hbar \vec{\nabla} (\mu_i(r)) d^3 r$$

$A \rightarrow S-ZKE$ initial HH, LH, SC

$$\vec{e}^0 \cdot \langle S | \vec{p} | -i \hbar \vec{\nabla} | -\frac{1}{\sqrt{2}} (P_x + i P_y) \rangle =$$

$$\langle \underline{S} | \underline{-i \hbar \frac{\partial}{\partial x}} | -\frac{1}{\sqrt{2}} (\underline{P_x} + i \underline{P_y}) \rangle$$



$$\langle S | -i \hbar \frac{\partial}{\partial x} | P_x \rangle = P_x$$

$$\langle S | -i \hbar \frac{\partial}{\partial x} | P_y \rangle = 0$$

$$HH \rightarrow S \left| \vec{e}^0 \cdot \langle i | \vec{P} | f \rangle \right| = e_x \cdot \left(-\frac{1}{\sqrt{2}} P_{cv} \right) + e_y$$

$e_z \rightarrow$

$$HH \rightarrow S \left| \vec{e}^0 \cdot \langle i | \vec{P} | f \rangle \right|^2 =$$

x-POLARIZED LIGHT $\frac{1}{2} P_{cv}^2$

y-POLARIZED LIGHT $\frac{1}{2} P_{cv}^2$

z-POLARIZED LIGHT \emptyset

$$LH \rightarrow S \left| \langle \underline{\uparrow} | -i \vec{\sigma} \cdot \vec{P} | \underline{\downarrow} \rangle \right| \frac{1}{\sqrt{6}} (P_x - iP_y) P_z$$

x-POL $\frac{1}{6} P_{cv}^2$

y-POL $\frac{1}{6} P_{cv}^2$

z-POL $\frac{4}{6} P_{cv}^2 = \frac{2}{3} P_{cv}^2$

Selection rules for interband transitions

The relevant matrix element is:

$$p_{if} = -i\hbar \int \psi_{\mathbf{k},i}^* \nabla \psi_{\mathbf{k},f} d^3r$$

$$J = \frac{e\hbar}{m} \nabla$$

$$\begin{aligned} |i\rangle &= \psi_{\mathbf{k}_i \ell} \\ &= e^{i\mathbf{k}_i \cdot \mathbf{r}} u_{\mathbf{k}_i \ell} \\ |f\rangle &= \psi_{\mathbf{k}_f \ell'} \\ &= e^{i\mathbf{k}_f \cdot \mathbf{r}} u_{\mathbf{k}_f \ell'} \end{aligned}$$

$$p_{if} = \hbar \mathbf{k}_i \int \psi_{\mathbf{k}_f \ell'}^* \psi_{\mathbf{k}_i \ell} d^3r - i\hbar \int u_{\mathbf{k}_f \ell'}^* (\nabla u_{\mathbf{k}_i \ell}) e^{i(\mathbf{k}_i - \mathbf{k}_f) \cdot \mathbf{r}} d^3r$$

Zero since Bloch states are orthogonal

2

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Selection rules for interband transitions

- Conduction band:

$$u_{c0} = |s\rangle$$

where $|s\rangle$ is a spherically symmetric state.

- Valence band:

$$\text{Heavy hole states: } |3/2, 3/2\rangle = \frac{-1}{\sqrt{2}} (|p_x\rangle + i|p_y\rangle) \uparrow$$

$$|3/2, -3/2\rangle = \frac{1}{\sqrt{2}} (|p_x\rangle - i|p_y\rangle) \downarrow$$

$$\text{Light hole states: } |3/2, 1/2\rangle = \frac{-1}{\sqrt{6}} [(|p_x\rangle + i|p_y\rangle) \downarrow - 2|p_z\rangle \uparrow]$$

$$|3/2, -1/2\rangle = \frac{1}{\sqrt{6}} [(|p_x\rangle - i|p_y\rangle) \uparrow + 2|p_z\rangle \downarrow]$$

From symmetry we see that *only* the matrix elements of the form

$$-\hbar \langle s | \frac{\partial}{\partial x} | p_x \rangle = -\hbar \langle s | \frac{\partial}{\partial y} | p_y \rangle = -\hbar \langle s | \frac{\partial}{\partial z} | p_z \rangle = p_{cv}$$

are different from zero.

3

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Selection rules for interband transitions

VB HH \rightarrow CB S

VB LH \rightarrow CB S

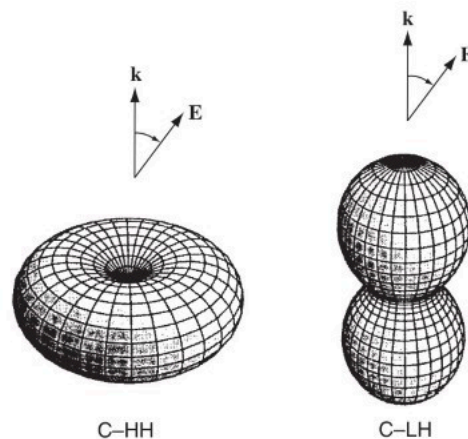
X pol	$\hbar^2 \left \langle s \frac{\partial}{\partial x} HH \rangle \right ^2 = \frac{1}{2} p_{cv}^2$	$\hbar^2 \left \langle s \frac{\partial}{\partial x} LH \rangle \right ^2 = \frac{1}{6} p_{cv}^2$
Y pol	$\hbar^2 \left \langle s \frac{\partial}{\partial y} HH \rangle \right ^2 = \frac{1}{2} p_{cv}^2$	$\hbar^2 \left \langle s \frac{\partial}{\partial y} LH \rangle \right ^2 = \frac{1}{6} p_{cv}^2$
Z pol	0	$\hbar^2 \left \langle s \frac{\partial}{\partial z} LH \rangle \right ^2 = \frac{2}{3} p_{cv}^2$

4

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Optical matrix element for HH and LH



HH states can be excited only by x,y polarized light

LH states can be excited by x,y and (predominantly) z polarized light

FIGURE A10.2: Dependence of the transition strength, $|M_T|^2$, on angle between the electron's k -vector and the incident electric field vector, \mathbf{E} , for C-HH and C-LH transitions (C-SO transitions are independent of angle). For C-HH transitions, $|M_T|^2$ is zero when $\mathbf{E} \parallel \mathbf{k}$ and becomes a maximum of $\frac{1}{2} \times |M|^2$ when $\mathbf{E} \perp \mathbf{k}$. For C-LH transitions, when $\mathbf{E} \parallel \mathbf{k}$, $|M_T|^2$ has a peak value of $\frac{2}{3} \times |M|^2$ and is reduced to $\frac{1}{6} \times |M|^2$ when $\mathbf{E} \perp \mathbf{k}$.

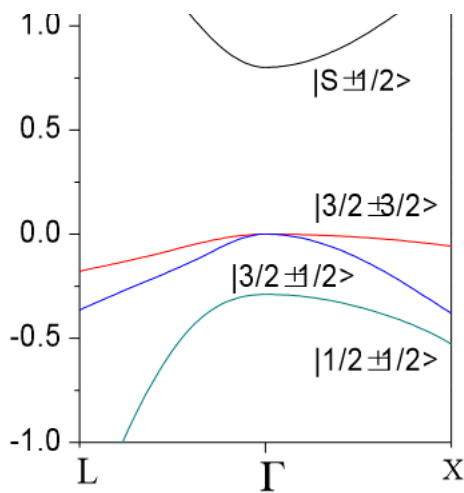
5

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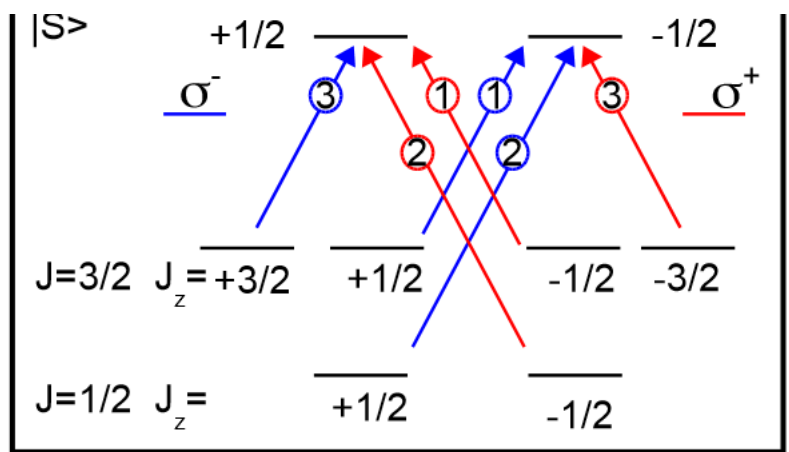
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Optical Spin Orientation





$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$



σ^- excitation
at Γ

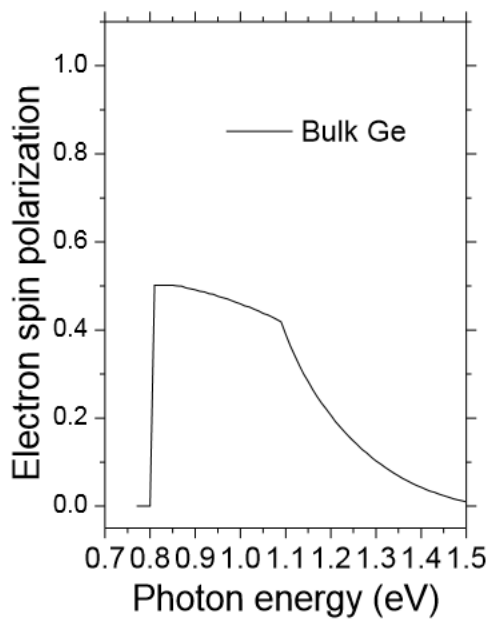
$$P = 0.5$$

6

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Optical Spin Orientation



$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$

σ^- excitation
at Γ

$$P = 0.5$$

7

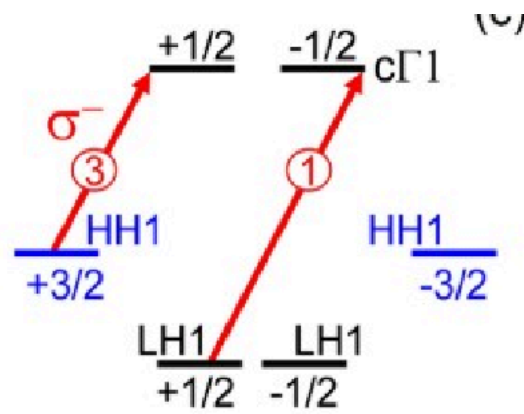
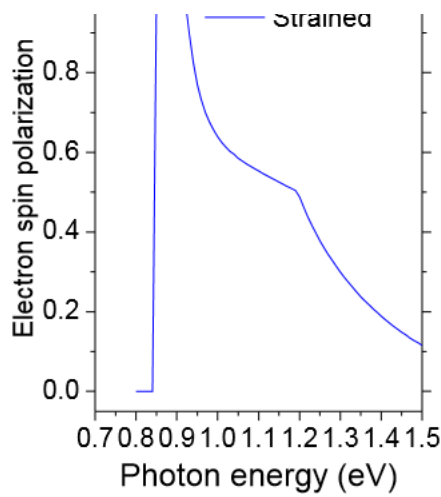
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Optical Spin Orientation



(c)



$$P = \frac{n_{\uparrow} - n_{\downarrow}}{n_{\uparrow} + n_{\downarrow}}$$

σ^- excitation
at Γ

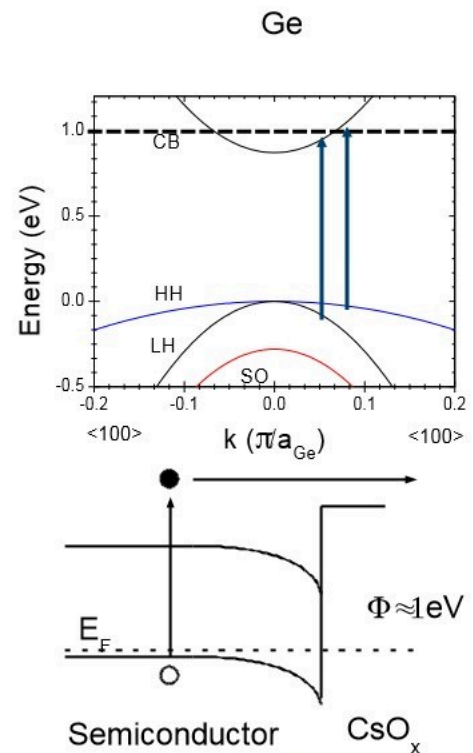
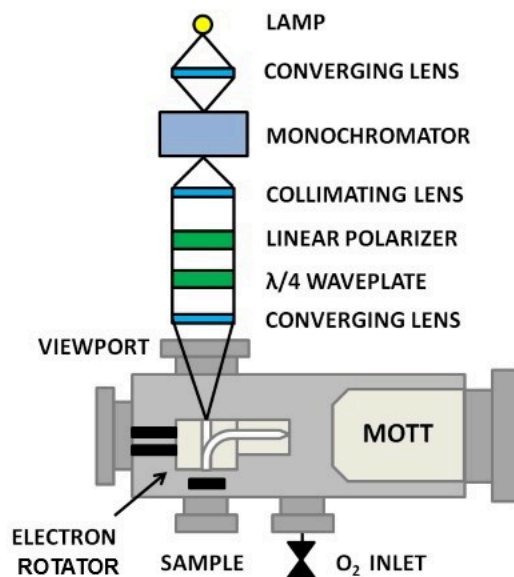
$$P=1$$

8

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Optical Spin Orientation: spin polarized photoemission

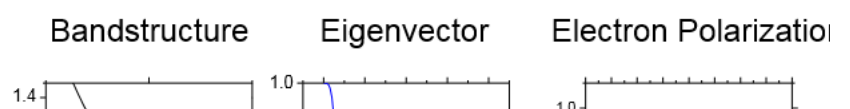


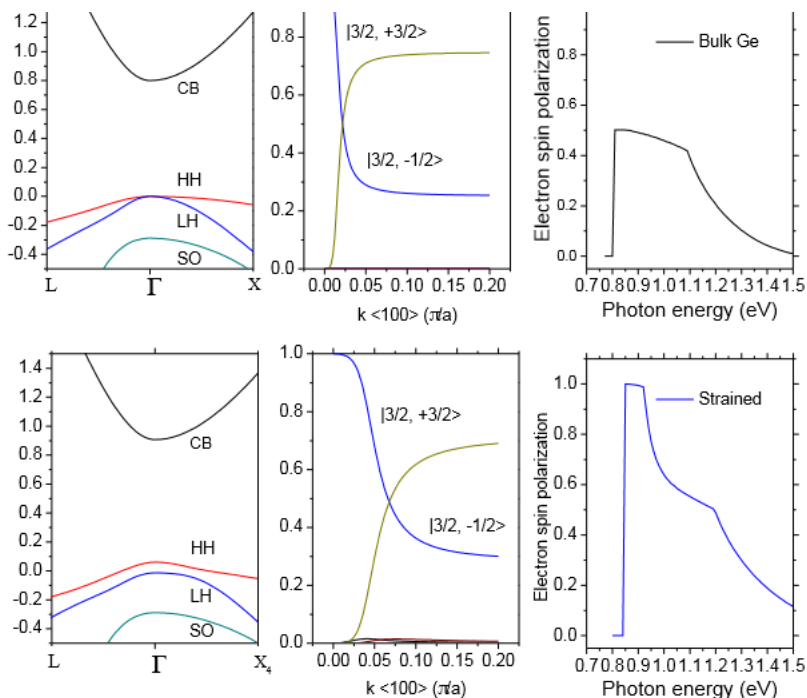
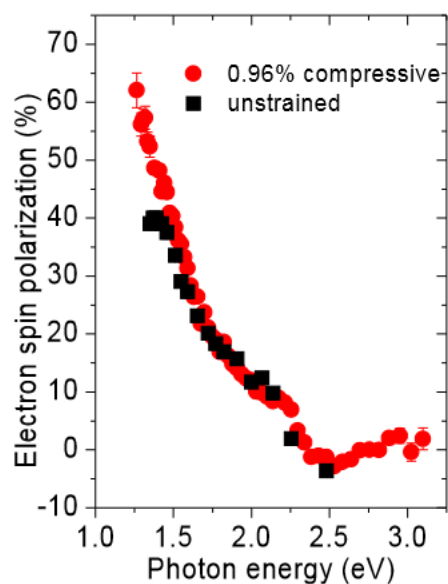
9

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Optical Spin Orientation: spin polarized photoemission



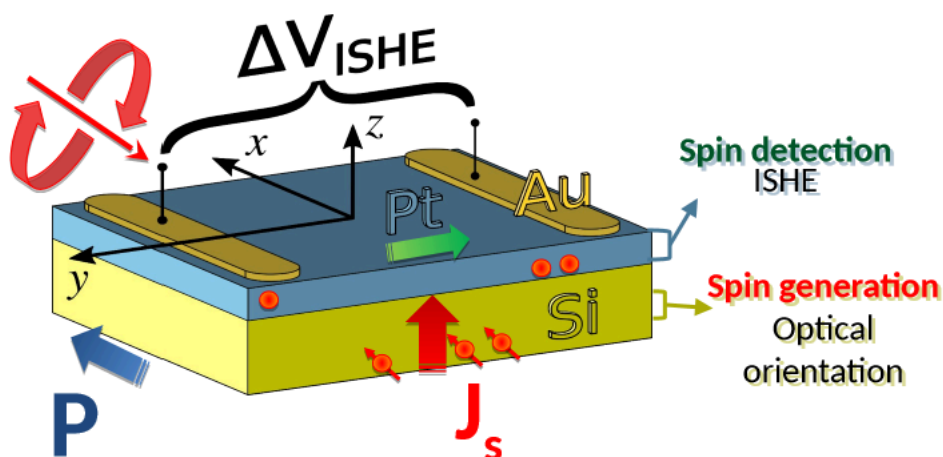


10

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Photo induced inverse spin Hall effect



$$\Delta V_{ISHE} \propto \gamma_{Pt} |J_s \times P|$$

Spin-to-charge conversion

Spin current

Spin polarization

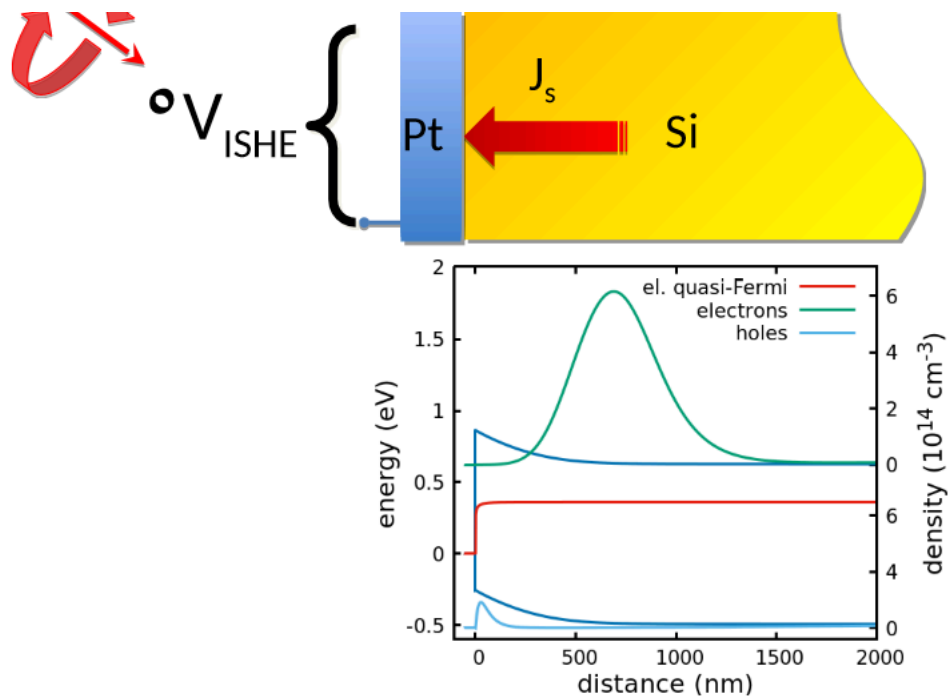
11

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Photo induced inverse spin Hall effect





12

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Photo induced inverse spin Hall effect

Charge drift-diffusion equations

Current eq.

$$J_n = -D_n \frac{\partial n}{\partial x} - \mu_n n E$$

$$J_p = -D_p \frac{\partial p}{\partial x} + \mu_p p E$$

Continuity eq.

$$\frac{\partial J_n}{\partial x} = SRH + \Phi_0 \alpha e^{-\alpha x}$$

$$\frac{\partial J_p}{\partial x} = SRH + \Phi_0 \alpha e^{-\alpha x}$$

Poisson

$$\frac{\partial E}{\partial x} = \frac{q}{\epsilon} (p + N_d - n)$$

$$SRH = w(x)(n_i^2 - np)$$

Spin drift-diffusion equations

Definitions

$$s = n_+ - n_-$$

$$J_s = J_{n+} - J_{n-}$$

Current eq.

$$J_s = -D_n \frac{\partial s}{\partial x} - \mu_n s E$$

Continuity eq.

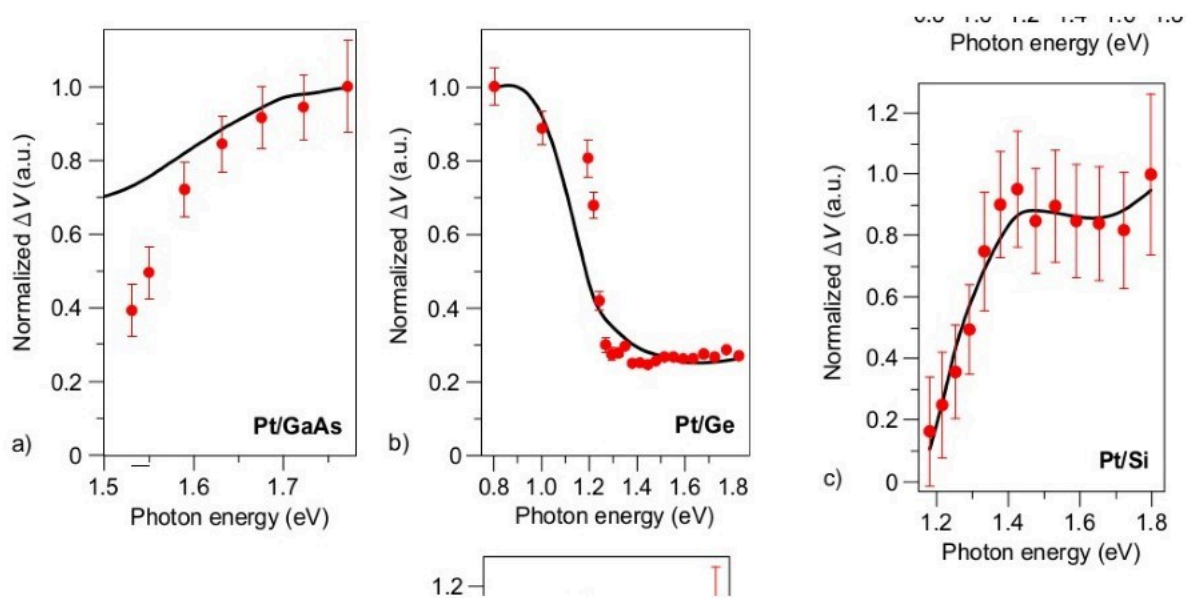
$$\frac{\partial J_s}{\partial x} = \frac{-s}{\tau_s} - w(sp) + P \Phi_0 \alpha e^{-\alpha x}$$

13

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Photo induced inverse spin Hall effect

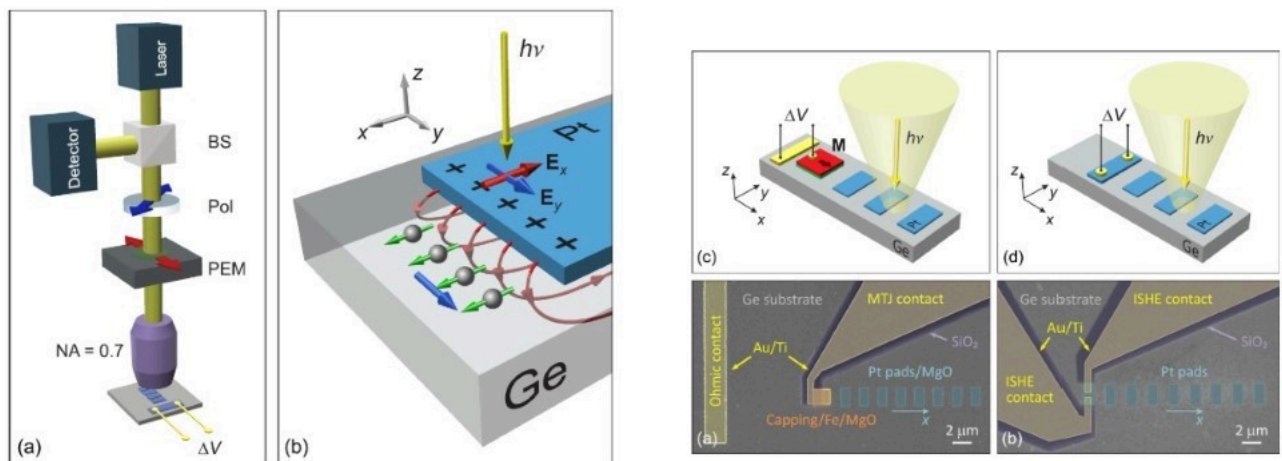


14

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Imaging spin diffusion



15

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Imaging spin diffusion

